

**Product Summary**

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

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Trench technology  
 $R_{DS(ON)}$  to minimize conductive loss

nd Synchronous Rectifier

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_C = 25$	7.5	A
	$I_D @ T_C = 75$	5.7	A
	$I_D @ T_C = 100$	4.7	A
Pulsed Drain Current	$I_{DM}$	30	A
Total Power Dissipation	$P_D @ T_C = 25$	8	W
Total Power Dissipation	$P_D @ T_A = 25$	1	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy @ $L = 0.1mH$	$E_{AS}$	10	mJ
ESD Level (HBM)		1A	



Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	15	° C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	120	° C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	260	° C

### Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.3		2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	1 2 . -	$V_{GS} = 10V, I_D = 10A$				
	1 2 . -	$V_{GS} = 4.5V, I_D = 6A$				
Forward Transconductance	$g_{FS}$	$V_{DS} = 10V, I_D = 4A$				

### Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
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Fig.1 Gate-Charge Characteristics

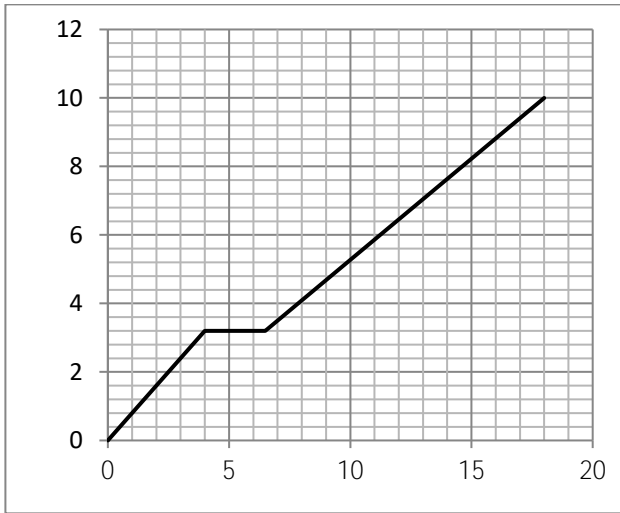


Fig.2 Capacitance Characteristics

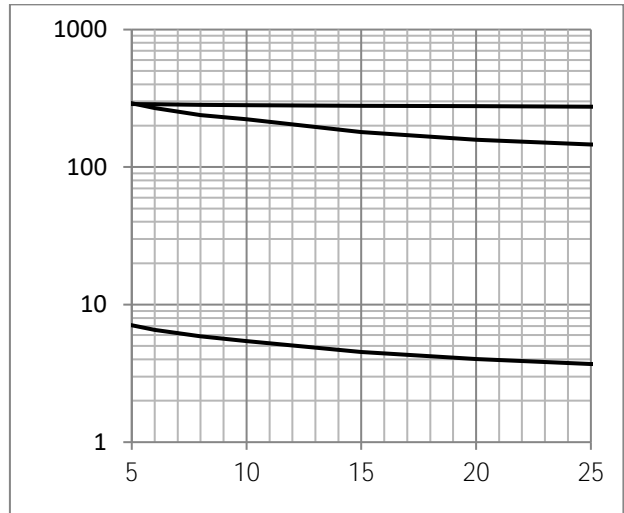


Fig.3 Power Dissipation

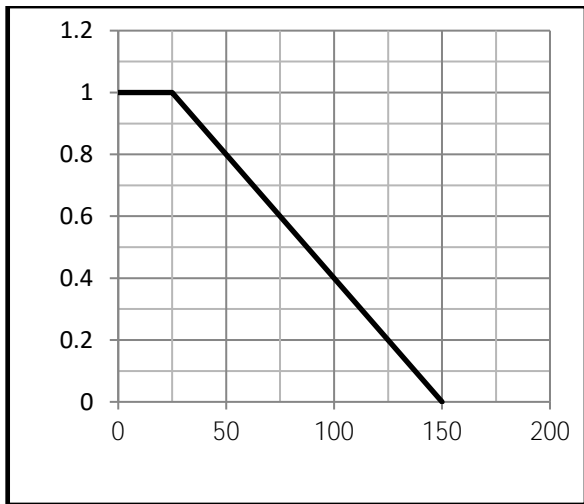


Fig.4 Typical output Characteristics

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Fig.5 Threshold Voltage V.S Junction Temperature

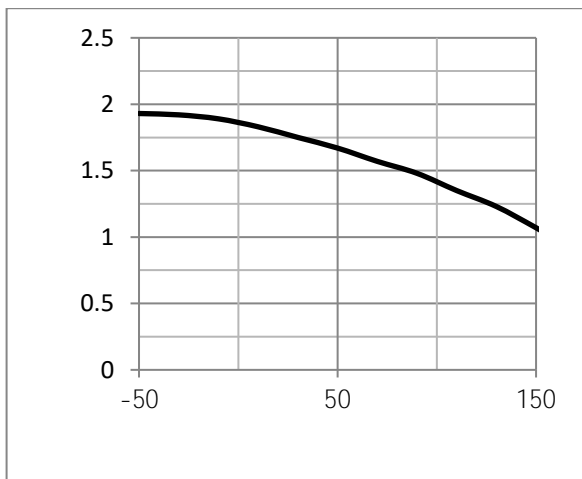


Fig.6 Resistance V.S Drain Current

F . 1D D52 D2 D5 FD

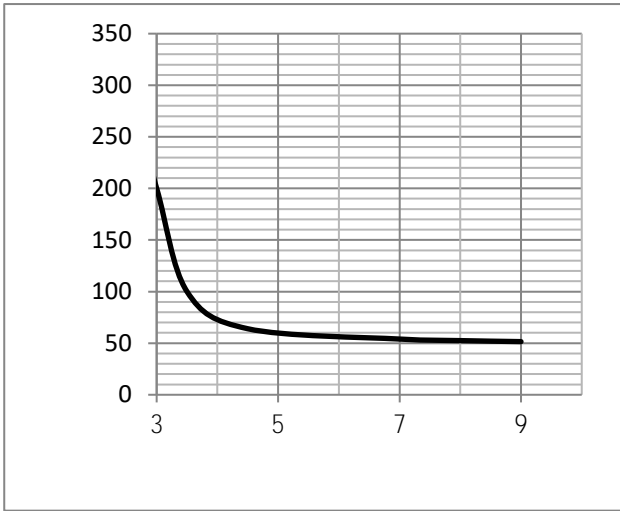


Fig.9 SOA Maximum Safe Operating Area

F . 1D D5 2 ) 3D D D

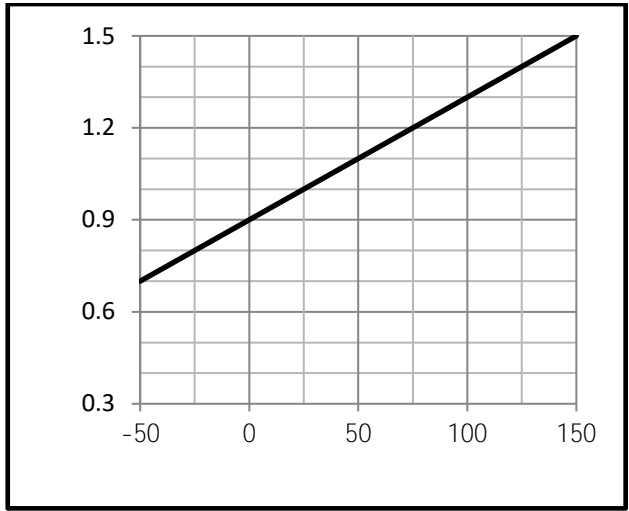
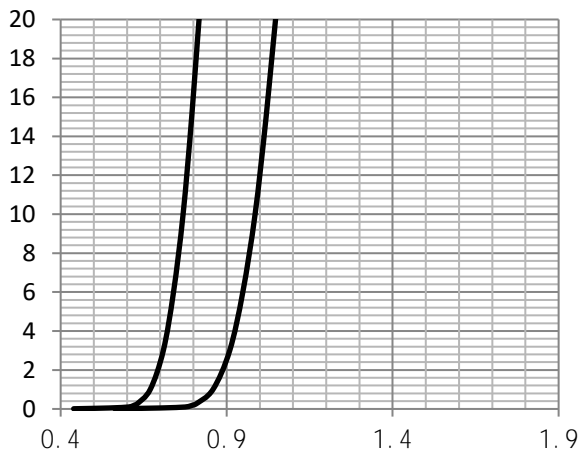


Fig.10 ID-Junction Temperature

F D CD C5 FD D



F D 3 ED G D

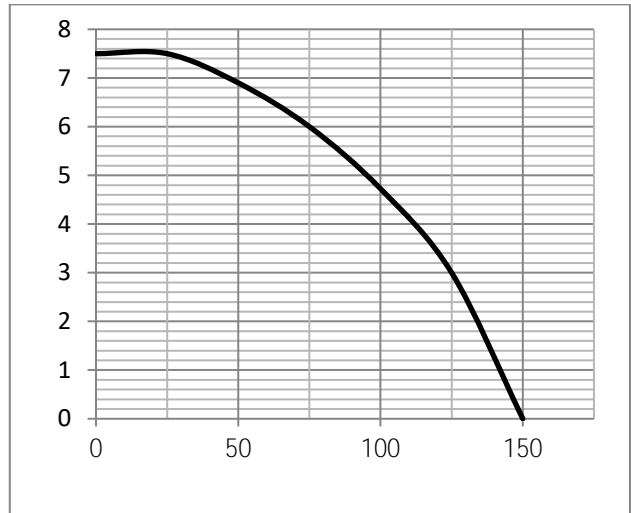


Fig.13 Switching Time Measurement Circuit

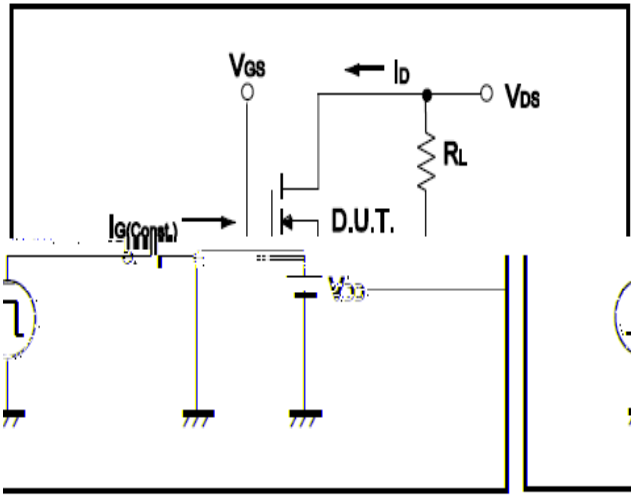


Fig.14 Gate Charge Waveform

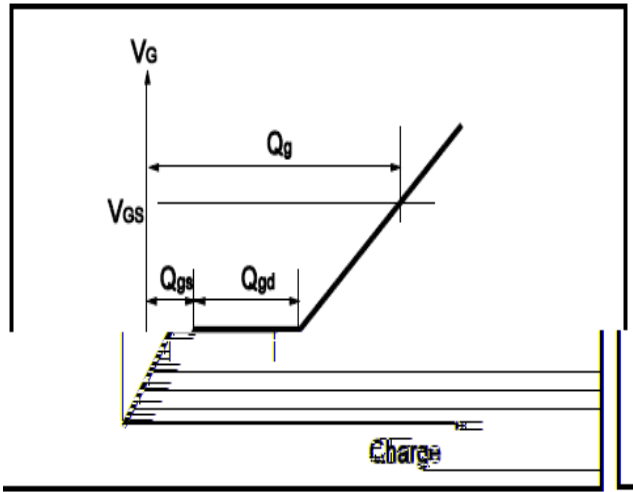


Fig.15 Switching Time Measurement Circuit

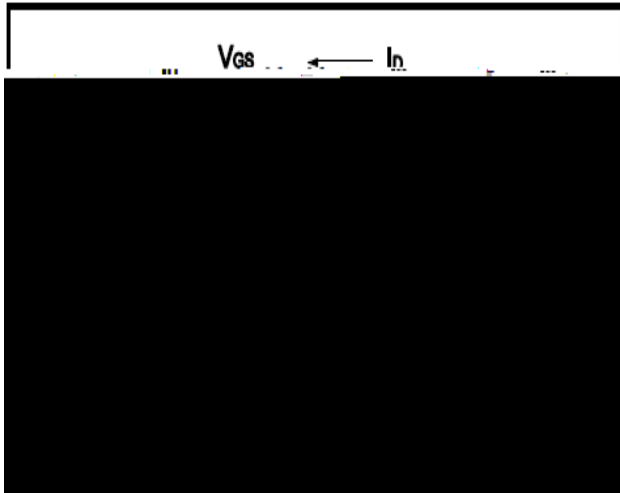
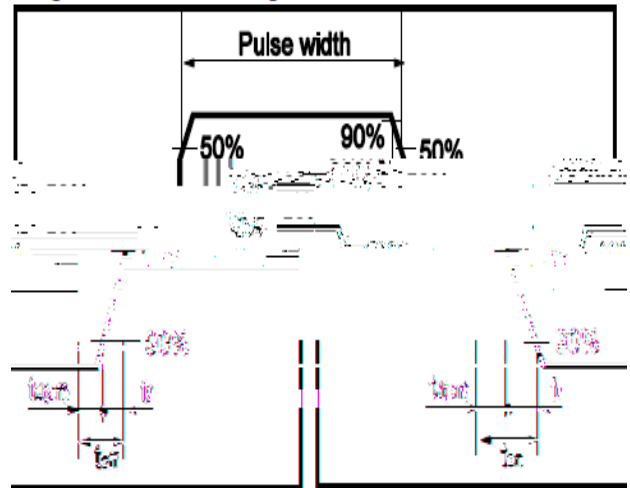


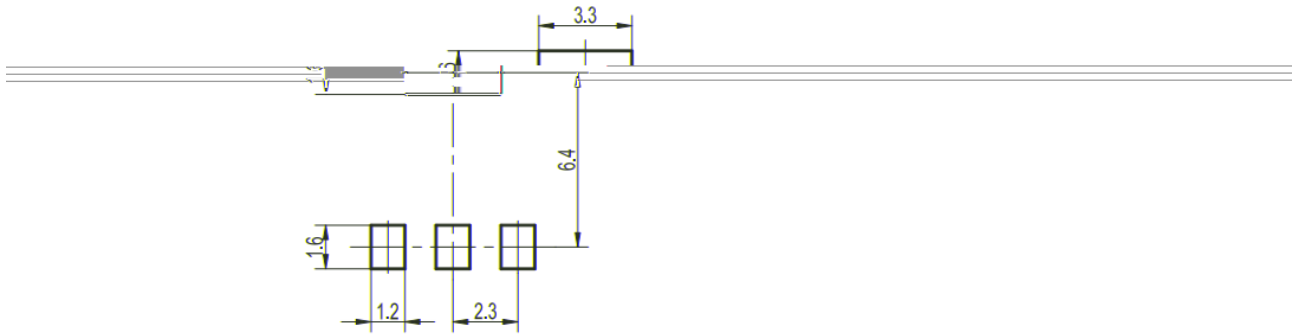
Fig.16 Gate Charge Waveform







**Recommended Soldering Footprint**



**Shipping information**

Dimension	Value	Dimension	Value	Dimension	Value	Dimension	Value	Dimension	Value
inch.	mm	inch.	mm	Per Reel	Packing Quantity	Package	Tape Width (mm)	mm	Pa
315 ± 0.004	330	13	330		3,000	SOT-223	12	8 ± 0.1	0.